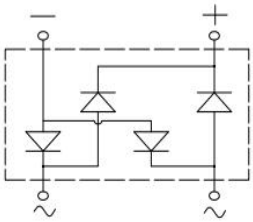
Bridge Rectifier Diode 整流桥





■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Reflow Solder Temperature 220℃ 回流焊温度 220 度
Package 封装: MBF

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	MB1F	MB2F	MB4F	MB6F	MB8F	MB10F	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	0.8						A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30						A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	90						℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	150℃,-55to+150℃						

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	V_F		1.1		V	I_F=0.8A
Reverse Current (T_A=25℃) 反向漏电流(T_A=125℃)	I_R			5 40	uA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D		13		pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

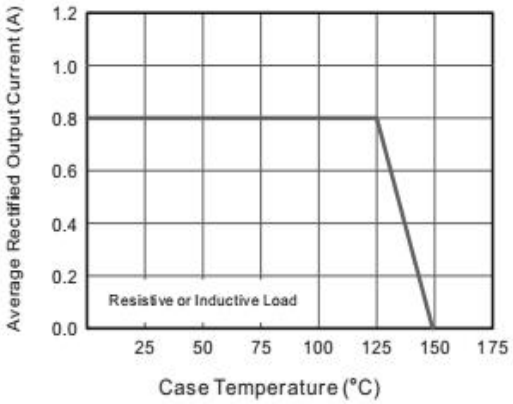


Figure 1: Forward Current Derating Curve

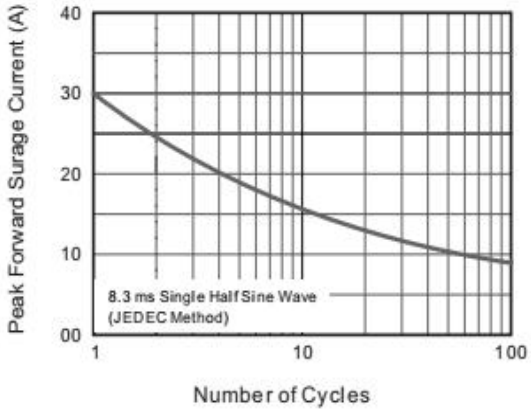


Figure 2: Peak Forward Surge Current

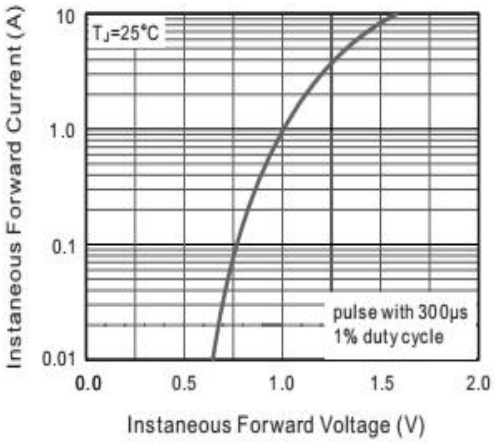


Figure 3:Instantaneous Forward Characteristics

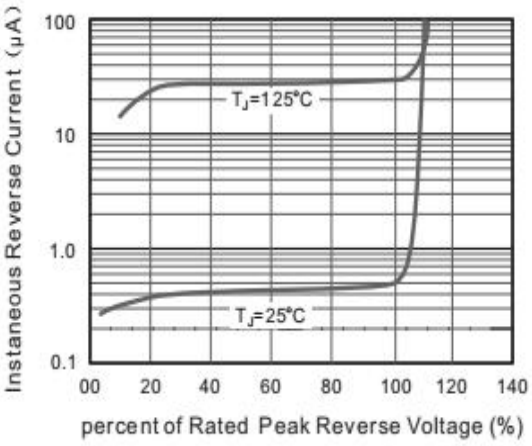


Figure 4: Reverse Leakage Characteristics

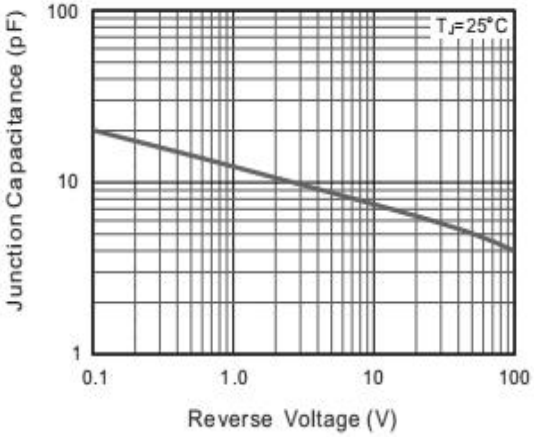
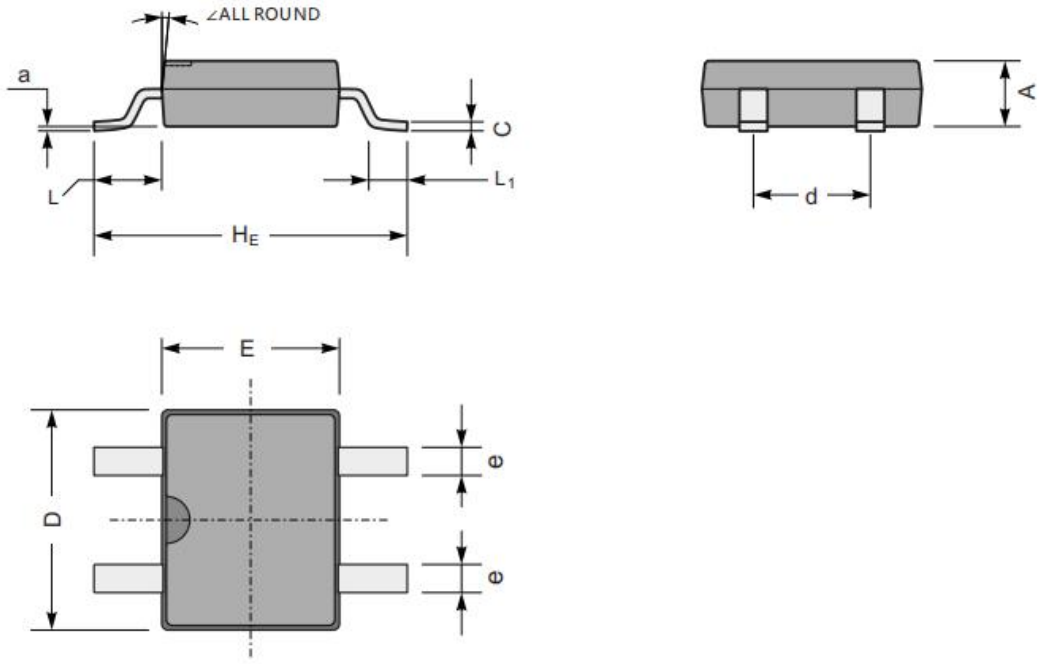


Figure 5: Junction Capacitance Characteristics

■Dimension 外形封装尺寸



MBF mechanical data

UNIT		A	C	D	E	H_E	d	e	L	L_1	a	∠
mm	max	1.6	0.22	5.0	4.1	7.0	2.7	0.8	1.7	1.1	0.2	7°
	min	1.2	0.15	4.5	3.6	6.4	2.3	0.5	1.3	0.5	—	
mil	max	63	8.7	197	161	276	106	31	67	43	8	
	min	47	5.9	177	142	252	91	20	51	20	—	